



General Description

The HFDP083N15AF102 use advanced SGT MOSFET technology to provide low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. This device is specially designed to get better ruggedness.

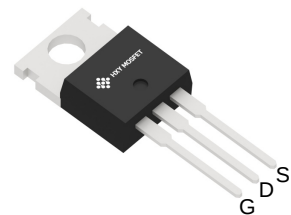
General Features

$V_{DS} = 150V$ $I_D = 120A$

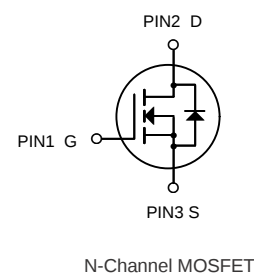
$R_{DS(ON)} < 11.5m\Omega @ V_{GS}=10V$

Applications

Consumer electronic power supply Motor control
Synchronous-rectification Isolated DC
Synchronous-rectification applications



TO-220



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
HFDP083N15AF102	TO-220	HXY MOSFET	50

Absolute Maximum Ratings at $T_J=25^{\circ}C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	V_{DS}	150	V
Gate source voltage	V_{GS}	± 20	V
Continuous drain current ¹⁾	I_D	120	A
Pulsed drain current ²⁾	$I_{D, pulse}$	352	A
Power dissipation ³⁾	P_D	178.6	W
Single pulsed avalanche energy ⁵⁾	EAS	204.8	mJ
Operation and storage temperature	T_{stg}, T_J	-55 to 150	$^{\circ}C$
Thermal resistance, junction-case	$R_{\theta JC}$	0.7	$^{\circ}C/W$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	52	$^{\circ}C/W$



Electrical Characteristics (T_J = 25°C, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	150	-	-	V
Gate-body Leakage Current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	I _{DSS}	V _{DS} = 150V, V _{GS} = 0V	-	-	1	μA
	T _J =100°C			-	-	100	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
Drain-Source On-Resistance ⁴		R _{DS(on)}	V _{GS} = 10V, I _D = 20A	-	9.5	11.5	mΩ
Forward Transconductance ⁴		g _{fs}	V _{DS} = 10V, I _D = 20A	-	69	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C _{iss}	V _{DS} = 75V, V _{GS} = 0V, f = 1MHz	-	3310	-	pF
Output Capacitance		C _{oss}		-	268	-	
Reverse Transfer Capacitance		C _{rss}		-	9.4	-	
Gate Resistance		R _g	f = 1MHz	-	3.2	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q _g	V _{GS} = 10V, V _{DS} = 75V, I _D = 20A	-	45	-	nC
Gate-Source Charge		Q _{gs}		-	15	-	
Gate-Drain Charge		Q _{gd}		-	8.5	-	
Turn-On Delay Time		t _{d(on)}	V _{GS} = 10V, V _{DD} = 75V, R _G = 3Ω, I _D = 20A	-	16	-	ns
Rise Time		t _r		-	12	-	
Turn-Off Delay Time		t _{d(off)}		-	30	-	
Fall Time		t _f		-	18	-	
Body Diode Reverse Recovery Time		t _{rr}	I _F = 20A, dI/dt = 100A/μs	-	76	-	ns
Body Diode Reverse Recovery Charge		Q _{rr}		-	182	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V _{SD}	I _S = 20A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	T _C = 25°C	I _S	-	-	-	120	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C
2. The EAS data shows Max. rating . The test condition is V_{DD}=50V, V_{GS}=10V, L=0.4mH, I_{AS}=32A.
3. The data tested by surface mounted on a 1 inch2 FR-4 board with 20Z copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
5. This value is guaranteed by design hence it is not included in the production test.



Typical Characteristics

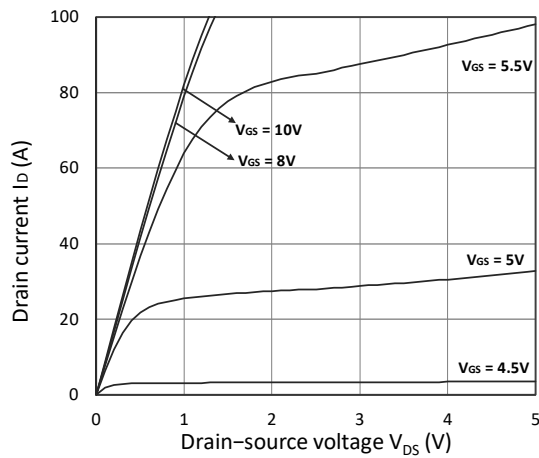


Figure 1. Output Characteristics

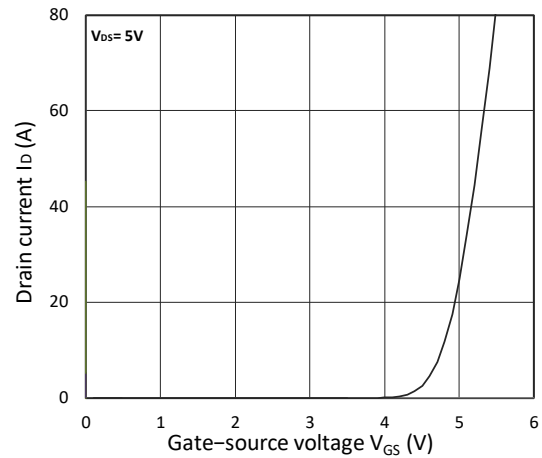


Figure 2. Transfer Characteristics

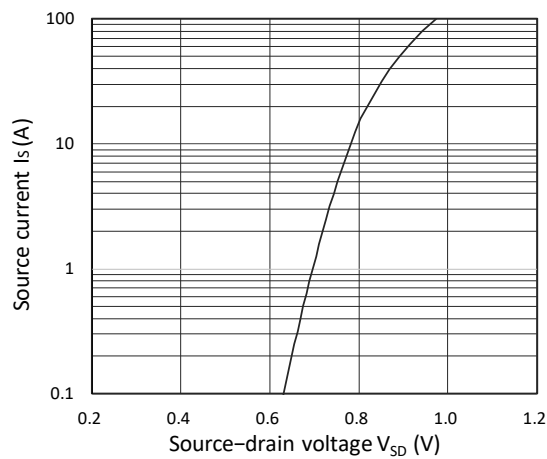


Figure 3. Forward Characteristics of Reverse

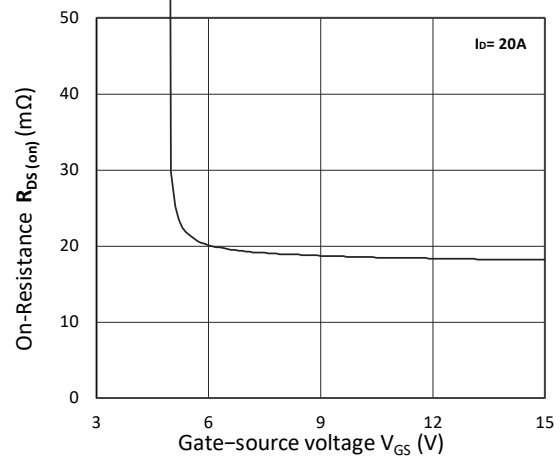


Figure 4. $R_{DS(on)}$ vs. V_{GS}

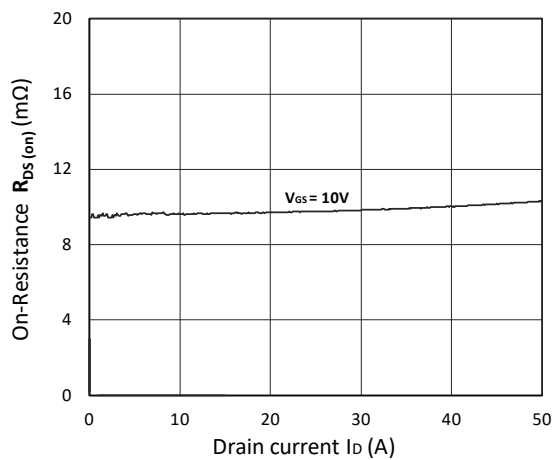


Figure 5. $R_{DS(on)}$ vs. I_D

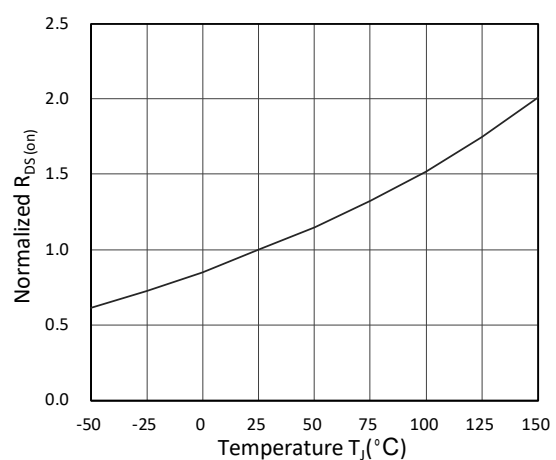


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

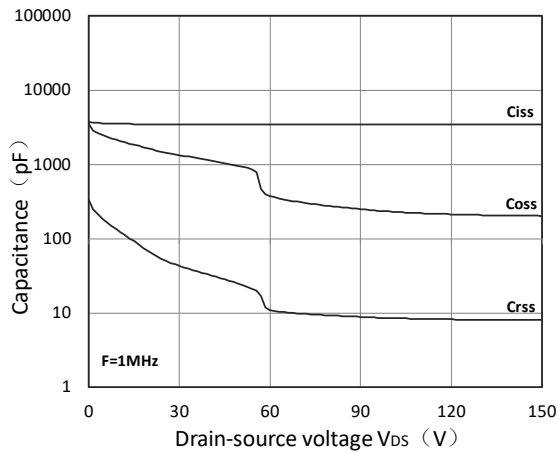


Figure 7. Capacitance Characteristics

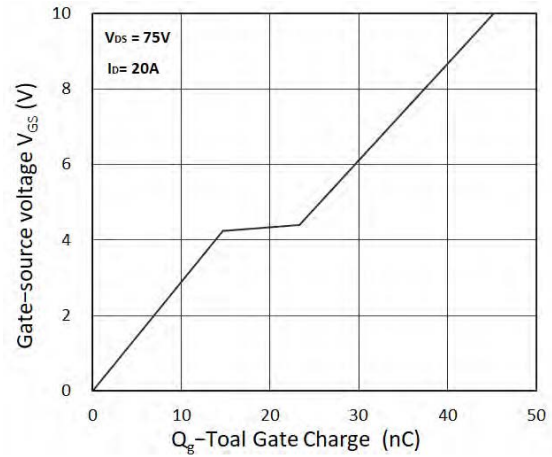


Figure 8. Gate Charge Characteristics

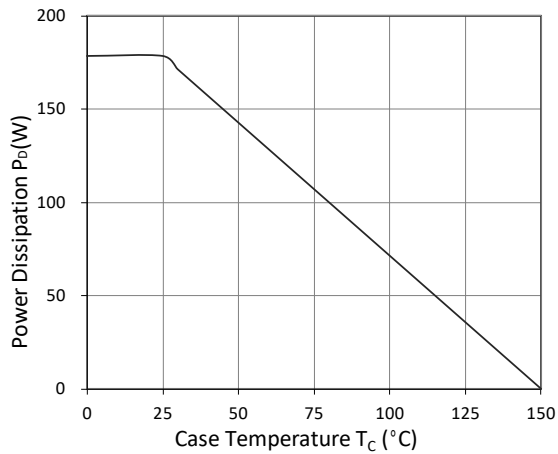


Figure 9. Power Dissipation

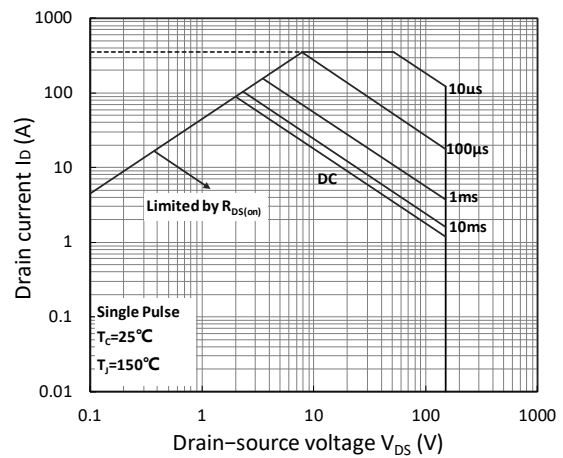


Figure10. Safe Operating Area

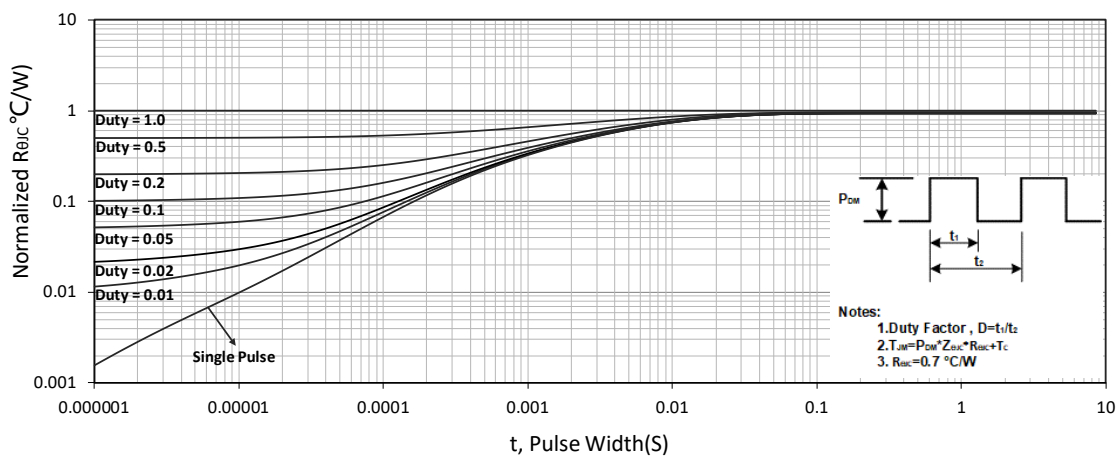


Figure 11. Normalized Maximum Transient Thermal Impedance



Test Circuit

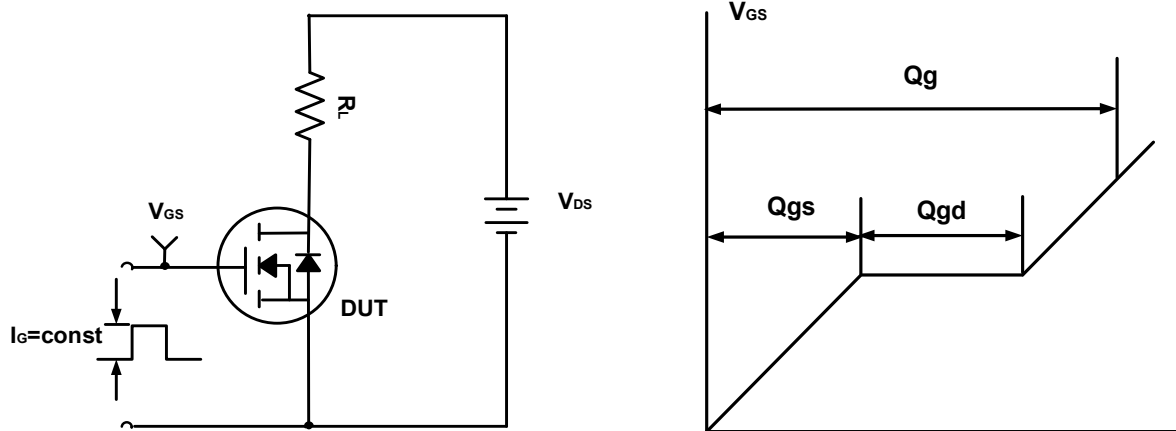


Figure A. Gate Charge Test Circuit & Waveforms

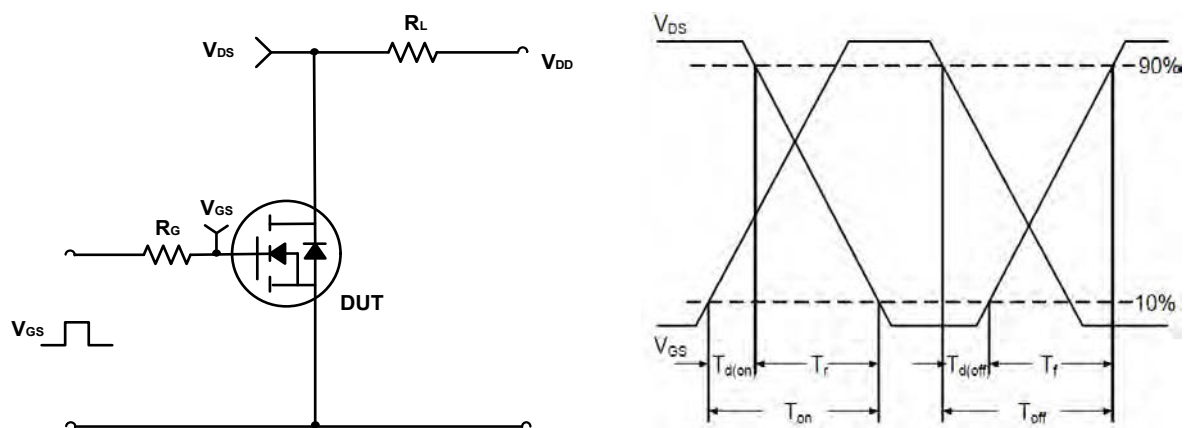


Figure B. Switching Test Circuit & Waveforms

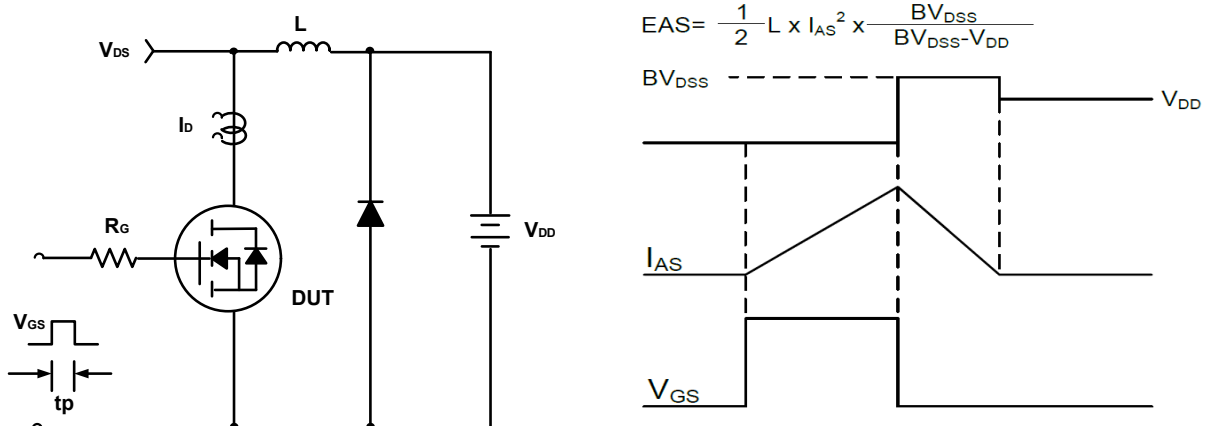
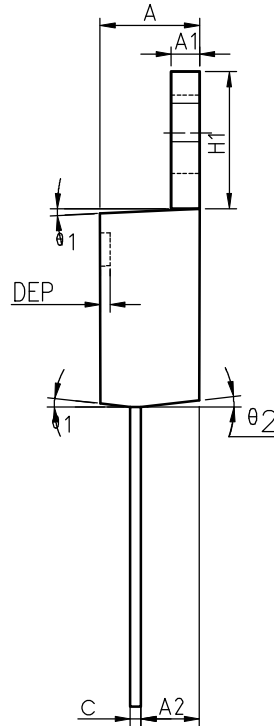
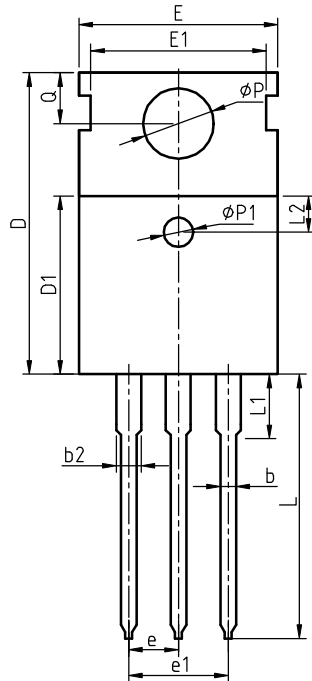


Figure C. Unclamped Inductive Switching Circuit & Waveforms



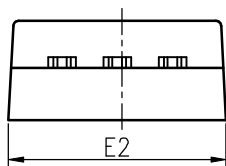
Package Information

TO-220



COMMON DIMENSIONS

SYMBOL	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	1.30	1.33	0.050	0.051	0.052
A2	2.35	2.40	2.50	0.093	0.094	0.098
b	0.77	0.80	0.90	0.030	0.031	0.035
b2	1.17	1.27	1.36	0.046	0.050	0.054
c	0.48	0.50	0.56	0.019	0.020	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.80	10.00	10.20	0.386	0.394	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.402
e		2.54	BSC		0.100	BSC
e1		5.08	BSC		0.200	BSC
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	13.50	13.65	0.502	0.531	0.537
L1	-	3.10	3.30	-	0.122	0.130
L2		2.50	REF		0.098	REF
P	3.50	3.60	3.63	0.138	0.142	0.143
P1	3.50	3.60	3.63	0.138	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.113
θ 1	5°	7°	9°	5°	7°	9°
θ 2	1°	3°	5°	1°	3°	5°
θ 3	1°	3°	5°	1°	3°	5°





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